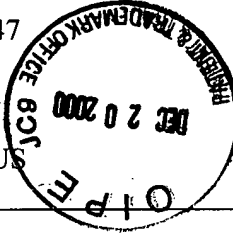


IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#14
1203-01
DRS

Applicant(s): Mark I. Gardner, Robert Dawson, H. Jim Fulford, Jr., Frederick N. Hause, Mark
W. Michael, Bradley T. Moore, Derick J. Wristers
Assignee: Advanced Micro Devices, Inc.
Title: Dopant Diffusion-Retarding Barrier Region Formed Within Polysilicon Gate
Layer
Serial No.: 09/177,047 Filing Date: October 22, 1998
Examiner: A. Ghyka Group Art Unit: 2812
Docket No.: M-4692 US Client Ref. No.: TT1618

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San Jose, California
December 20, 2000

BOX CPA TO 3600 MAIL ROOM
COMMISSIONER FOR PATENTS
Washington, D. C. 20231

INFORMATION DISCLOSURE STATEMENT
UNDER 37 CFR § 1.97(b)

Dear Sir:

Pursuant to 37 C.F.R. § 1.56, § 1.97 and § 1.98, the documents listed on the accompanying PTO Form-1449 are called to the attention of the Examiner for the above patent application. Copies of these documents are enclosed.

Citation of these documents shall not be construed as:

1. an admission that the documents are necessarily prior art with respect to the instant invention;
2. a representation that a search has been made, other than as described above; or
3. an admission that the information cited herein is, or is considered to be, material to patentability as defined in § 1.56(b).

EXPRESS MAIL LABEL NO:

EL708268675US

Respectfully submitted,

David G. Dolezal
Attorney for Applicant(s)
Reg. No. 41,711

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DEC 29 2000

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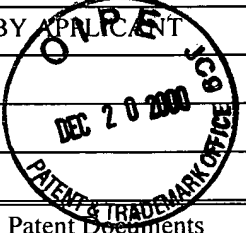
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| | | | | | M-4692 US | | 09/177,043 | |
| INFORMATION DISCLOSURE STATEMENT BY APPLICANT | | | | | Applicant(s) | | | |
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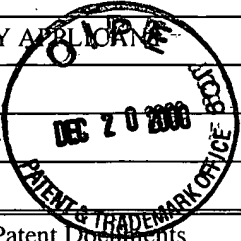
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